

# Snapdragon 820 SEE Testing and On-Site Stuck Bit Mitigation

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# Outline

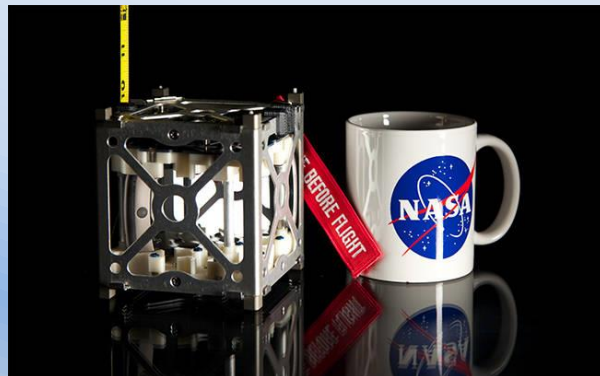
- Background and Motivation
- Test Setup
- Testing – What happened? & on-site issues
- Problem Solving
- Results
- Future Work
- Conclusions

# Motivation

- Device built on Samsung 14 nm Low Power Plus (LPP) FinFET platform – fabrication info
- Very low power system (<5 W)
- Vehicle for exploring ARM/Snapdragon architecture



Snapdragon Flight  
- Qualcomm



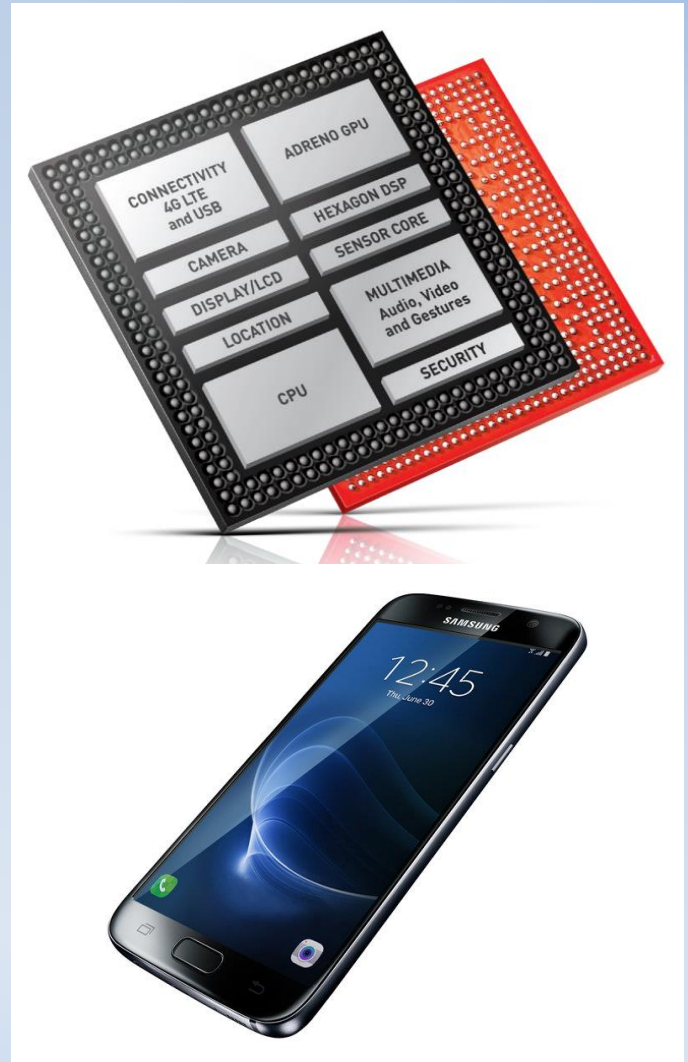
phonesat 2.5



image – vr-zone.com

# Background: Snapdragon 820

- Key Features:
  - Quad-core Kryo CPU
    - Actually has ~9 distinct processors
    - big.LITTLE – 2 cores are faster, bigger, other two are smaller and slower
  - Low power DDR4
  - Universal Flash Storage
  - Hexagon 680 DSP with isolated sensor power
  - Camera controller
  - Hardware multimedia encode & decode

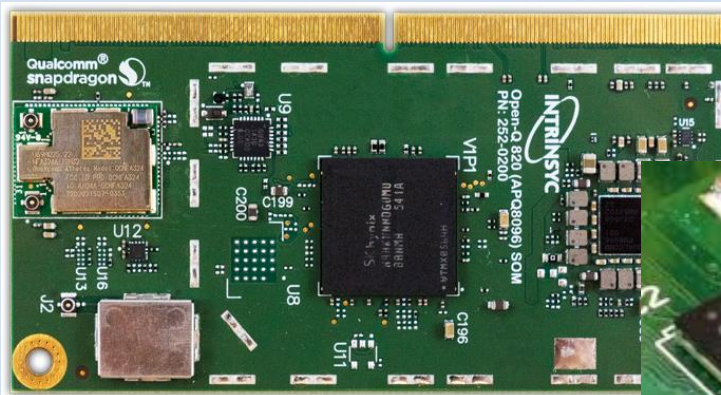




# Background:

## Intrinsyc Open-Q 820

- Evaluation board for Snapdragon 820
- Hardware debug intentionally limited
- Uses system-on-module/carrier configuration
- 3GB DDR4 with POP setup

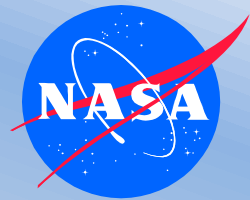




# Background: Tests Performed

- Heavy Ions @ TAMU
  - Ion selection  
range limited...
  - Android & custom code
- Protons @ MGH
  - $\sim 1 \times 10^{10}$  /cm<sup>2</sup> with 100, and 200 MeV,  $5 \times 10^9$ /cm<sup>2</sup> with 50 MeV
  - Android & custom code
- Neutrons at LANSCE
  - $\sim 1 \times 10^{11}$  /cm<sup>2</sup> with sea level neutron spectrum

Beam	LET (MeV-cm <sup>2</sup> /mg)	Exposure (cm <sup>2</sup> )
N	1	1.2E+07
Ne	6	1.2E+04
Ar	15	4.1E+04



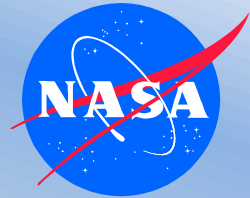
# Heavy Ion Setup

## - Device Stack Estimate

Item	Material	Range of Thicknesses	
		Low	High
Beam Port	Aramica	25.4 $\mu\text{m}$	
Air	Air	3 cm	
DDR3 Top Plastic	Plastic	100 $\mu\text{m}$ (1.18 g/cm <sup>3</sup> )	300 $\mu\text{m}$ (1.85 g/cm <sup>3</sup> )
DDR3 Die	Silicon	250 $\mu\text{m}$	400 $\mu\text{m}$
DDR3 Metalization	Aluminum	40 $\mu\text{m}$	60 $\mu\text{m}$
Air Gap	Air	100 $\mu\text{m}$ (1.18 g/cm <sup>3</sup> )	300 $\mu\text{m}$ (1.85 g/cm <sup>3</sup> )
Snapdragon Top Plastic	Plastic	100 $\mu\text{m}$	300 $\mu\text{m}$
Snapdragon Die	Silicon	500 $\mu\text{m}$	800 $\mu\text{m}$

	LET (MeV-cm <sup>2</sup> /mg)		Range ( $\mu\text{m}$ Si)	
	Minimum	Maximum	Maximum	Minimum
N-40 MeV	0.74	1.2	1380	448
Ne-40 MeV	1.8	9	701	Out of Range
Ar-40 MeV	10	20	123	Out of Range

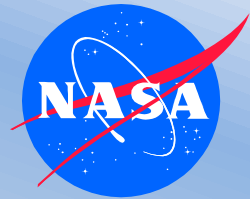
- Using estimated thicknesses to get a range of estimated LETs
- Heavy ion testing (thus far) is general info, so it was most important to show chance of reaching sensitive region



# Software Development

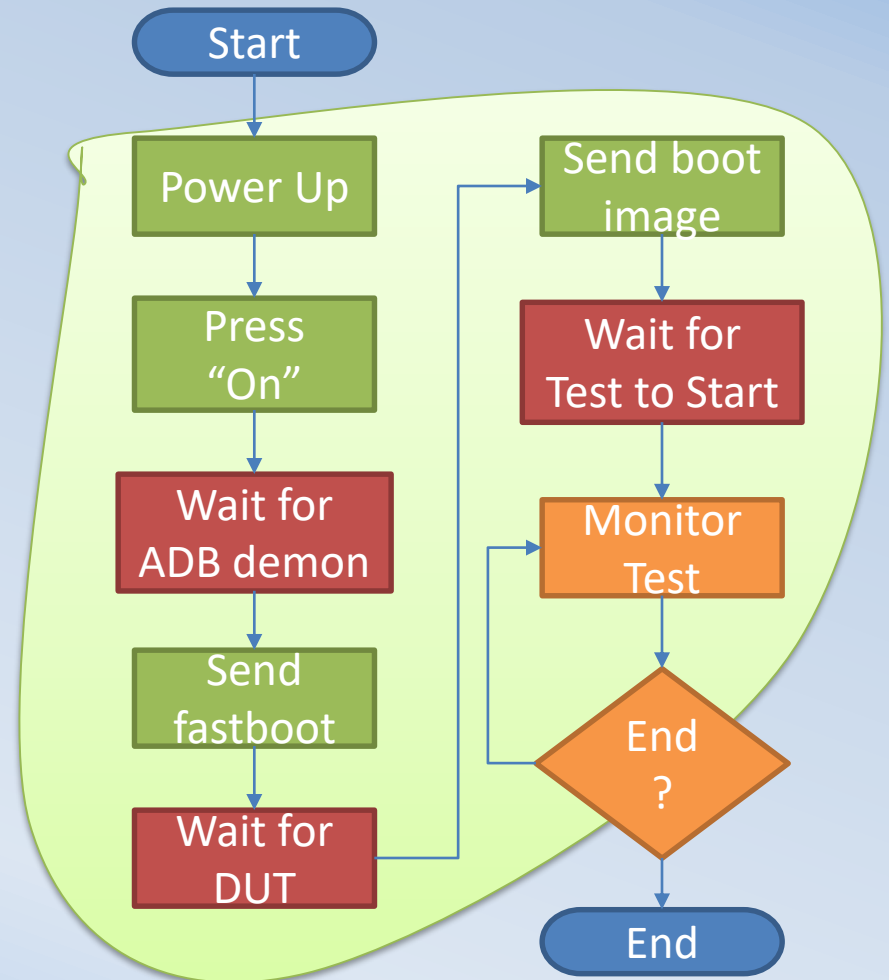
- We used Android to initialize the test boards
  - Some testing put the test code before Android, but the data was difficult to work with
  - Later, test code was moved to after Android had brought up I/O
  - During neutron testing we disabled additional cores once we realized we were getting crashes from them
- Software approach is to inject code into boot loader
  - Done by modifying boot binary file directly
- Specific test software items:
  - Memory tests, with L1 cache enabled, @16kB, 64kB, 256kB, and 1GB
  - Let Android run

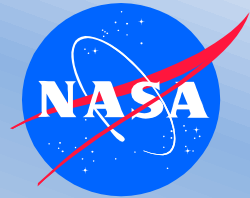




# Test Boot/Run

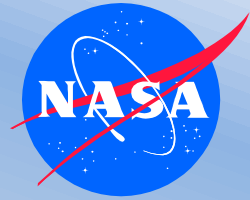
- Booting was somewhat tricky
- Wanted to avoid bricking the boards, so we never changed the on-board software
- 8 Test System States





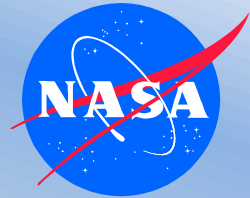
# Observation: Crashes

- Every operating condition had crashes
  - Mostly these involved the test DUT no longer communicating
  - On later tests, we were able to use Android's exception handlers to get some indication what was going on
- Required restarting the test after each crash
  - We developed an automated system to do this at LANSCE
  - System conditions/handling was complex for the 8 states and possible errors coming from each
  - At LANSCE this all had to be done while being irradiated



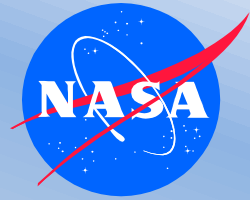
# Handling Crashes

- Once we were able to isolate cause of crashes
  - This occurred during testing at LANSCE where we could observe the exception messages
  - Also, we were able to tell the exception handlers to return to the test code.
- Most common exceptions were observed to come from CPUs that were not being tested
  - Instructed Android to not boot unnecessary CPUs
- Remaining exceptions were caused primarily by memory access errors



# Observation: Stuck Bits

- We targeted the DDR4 device for data, because it had to be exposed regardless
  - This is frustrating because it really is not helpful to have two sources of errors
  - But the DDR4 device provided stuck bits as well as SBUs
- Proton and neutron testing → about as many stuck bits as SBUs
  - Stuck bits caused the DUTs to have trouble booting
  - Usually a reasonable chance to get a handful of detectable stuck bits before a DUT was unable to boot
  - Android appears to have a retry option on some memory allocation to allow it to avoid bad memory regions

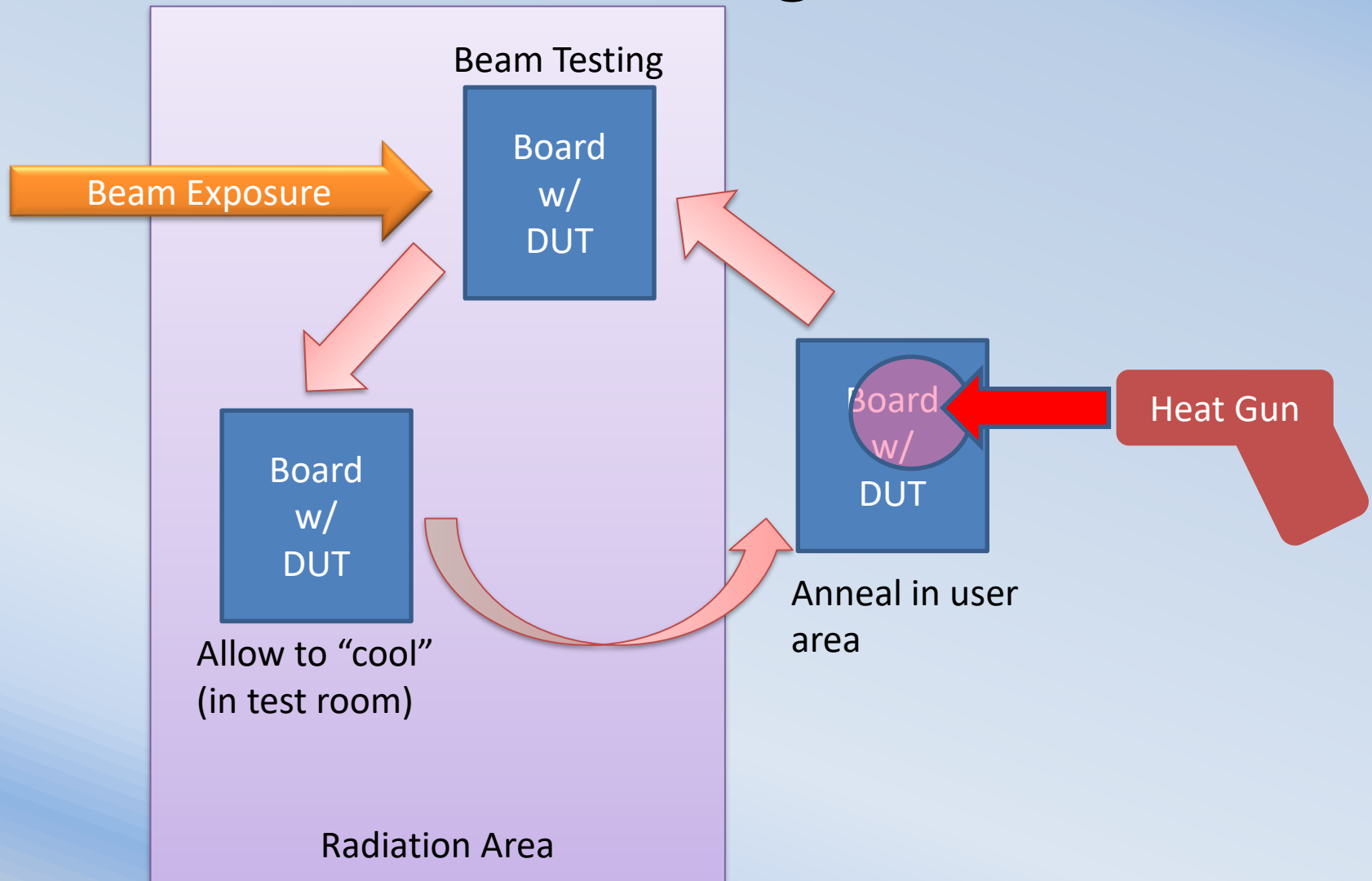


# Handling Stuck Bits

- Stuck bits were observed once we were able to get the test system reading 1 GB (out of 3 GB) of the device memory.
- Were able to determine that earlier failures of DUTs were likely due to stuck bits interfering with boot processes.
- Developed methods to anneal stuck bits in-situ, requiring a rotation of boards at LANSCE to facilitate automated testing.

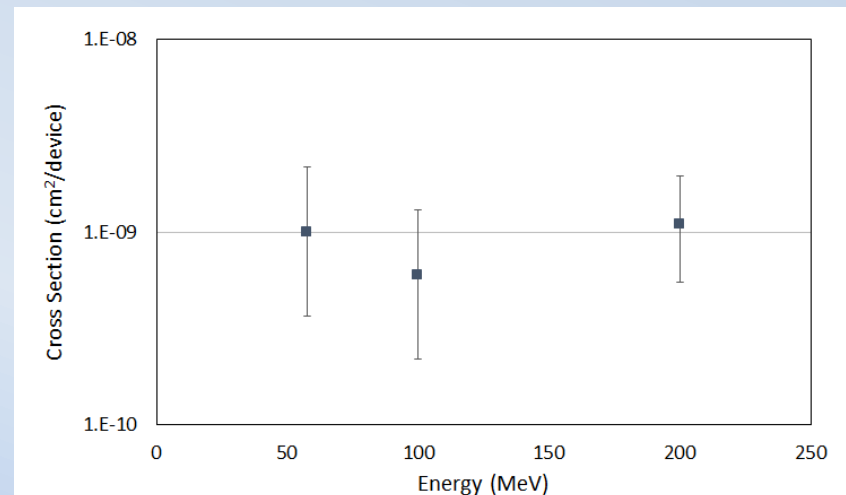
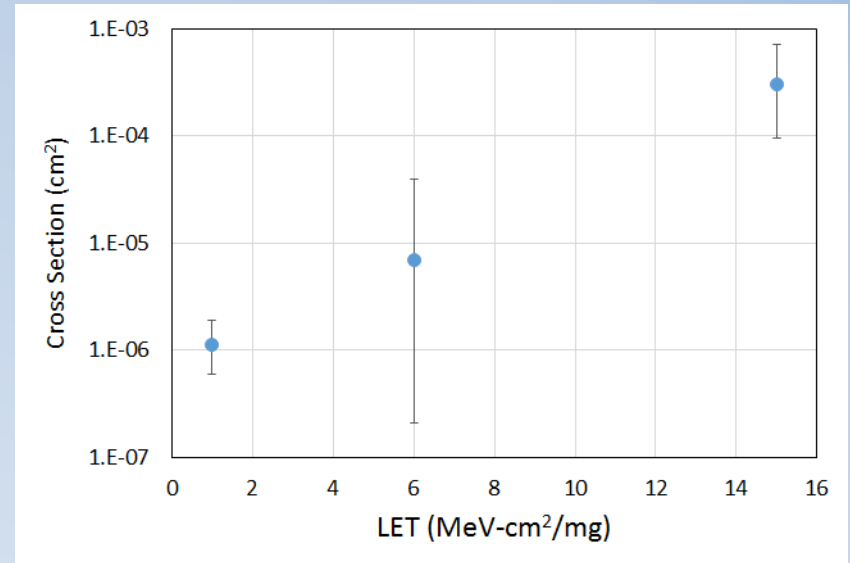


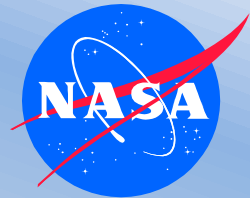
# Stuck Bit Annealing



# Results: Crashes

- Heavy Ions:
    - Proton curve →
    - Neutrons
- $\sigma \sim 1 \times 10^{-8} / \text{cm}^2$

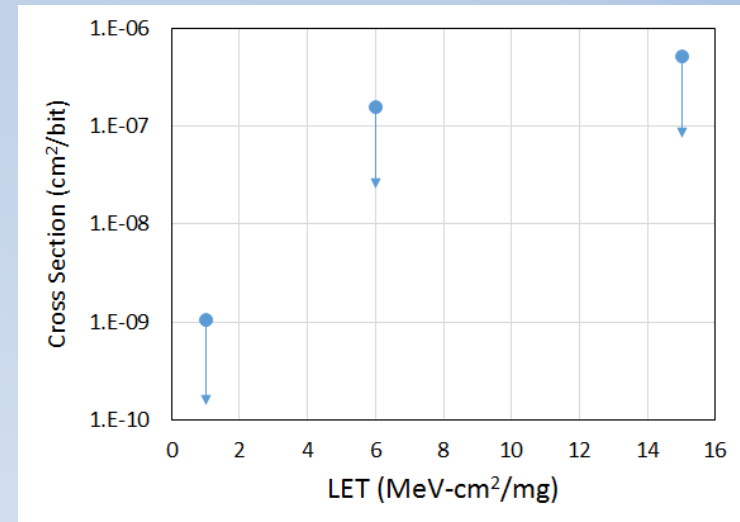




# Results:

## SBU & Stuck Bits

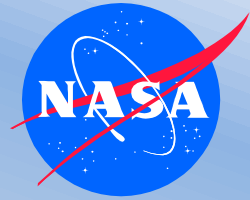
- Limiting  $\sigma$  for SBUs in Snapdragon:



- Stuck Bits during Boot & Anneal:

Board	Incr. Neutron Exposure (/cm2)	Annealing		Stuck Bits - boot	
		Duration (mins)	Temp ( C )	Before	After
2	2.52E+10	30	175	13	1
1	2.52E+10	15	175	14	3
1	0.00E+00	90	175	3	0
4	3.12E+09	120	175	3	0
5	2.81E+10	220	175	8	0

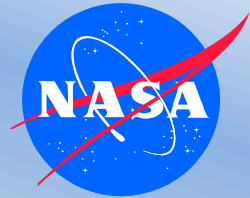
- Note also crunching data on bit errors in the 1GB memory region



# Future Work

## Heavy Ion Testing

- Improved test system will enable testing with heavy ions
  - Registers
  - Crashes (with capture of exceptions)
  - DDR4 Errors
- Additional data on caches
  - We have modified cache test code, but so far the L1 caches have not shown bit errors
    - May have ECC or parity masking the errors
- Test code on all cores?



# Conclusion

- Snapdragon 820 test development
  - How to deal with package on package – blast through it
  - Software – able to put custom low-level software in beam
- System results
  - Primary events observed – crashes, and bit errors in DDR4
  - Stuck bits also observed in DDR4
    - Sometimes Android was able to map around these during boot
  - No cache bit errors observed
- In-situ test development to improve data
  - On-site annealing of stuck bits used to recover boot
  - Automated exception responses to enable continuing test